NSN 5961-01-031-5011

Diode Semiconductor Device - Page 1 of 2

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Inclosure Material:

Metal

Overall Length:

0.450 inches

Overall Diameter:

0.667 inches

End Application:

An/urc-85 fscm 13499

Mounting Facility Quantity:

1

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case

Overall Width Across Flats:

Between 0.667 inches and 0.687 inches

Thread Size:

0.250 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

95.6 breakdown voltage, dc

Current Rating Per Characteristic:

530.00 milliamperes repetitive peak forward current

Power Rating Per Characteristic:

50.0 watts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius case

Test Data Document:

81349-mils19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Thread Series Designator:

Unf

Terminal Type And Quantity:

1 threaded stud and 1 tab, solder lug

Specification Data:

81349-mil-s-19500/358 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0